L Number	Hits	Search Text	DB	Time stamp
-	4200	(438/17,18,11,for.101,for.102,for.142).CCLS.	USPAT;	2003/08/28 11:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	4	((438/17,18,11,for.101,for.102,for.142).CCLS.) and LOCOS	USPAT;	2003/08/27 13:54
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(10014710115 1015 1015 11015 11015 11015	IBM_TDB	2002/00/27 44-20
-	36	((438/17,18,11,for.101,for.102,for.142).CCLS.) and field	USPAT;	2003/08/27 14:29
		near2 (oxidat\$4 oxydat\$4 insulat\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	10	//420/17 19 11 for 101 for 102 for 1/2\ CCLC \ and for not	IBM_TDB USPAT;	2003/08/27 14:13
-	18	((438/17,18,11,for.101,for.102,for.142).CCLS.) and fox not	US-PGPUB;	2003/06/27 14.13
		(((438/17,18,11,for.101,for.102,for.142).CCLS.) and field	EPO; JPO;	*
		near2 (oxidat\$4 oxydat\$4 insulat\$4))	DERWENT;	
			IBM_TDB	
l _	0	(Etching etched etch) near2 substrate with (fox locos field	USPAT;	2003/08/28 09:43
-	١	near (oxide oxidation oxyde oxydation)) near2 mask	US-PGPUB;	2000,00,20 05.10
		Tical (Oxide Oxidation Oxyde Oxydddion)) Tical 2 maos	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	36	(Etching etched etch) near2 substrate with (fox locos field	USPAT;	2003/08/27 15:06
	30	near (oxide oxidation oxyde oxydation)) near2 mask	US-PGPUB;	
		Theat (oxide oxidation) oxyde oxydddion), mear a mae'r	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	5652458.URPN.	USPAT	2003/08/27 15:00
-	1	"5200351".PN.	USPAT	2003/08/27 15:00
-	6	5563080.URPN.	USPAT	2003/08/27 15:00
-	5	("3861024"   "3958040"   "3980508"   "4242156"	USPAT	2003/08/27 15:00
		"4313256"   "4667395"   "5132238"   "5200351").PN.		
-	17	(5652458.URPN. "5200351".PN. 5563080.URPN.	USPAT;	2003/08/27 15:00
		(("3861024"   "3958040"   "3980508"   "4242156"	US-PGPUB;	
}		"4313256"   "4667395"   "5132238"   "5200351").PN.) ) not	EPO; JPO;	
		((Etching etched etch) near2 substrate with (fox locos field	DERWENT;	
		near (oxide oxidation oxyde oxydation)) near2 mask )	IBM_TDB	2002/02/27 :- :-
-	42	(Etching etched etch) near2 (silicon si) with (fox locos field	USPAT;	2003/08/27 15:07
		near (oxide oxidation oxyde oxydation)) near2 mask	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(/Pid ) - Asked stalk) 0 (-9) 0 (-1) (f. 1 0.1)	IBM_TDB	2002/00/27 45:07
-	29	((Etching etched etch) near2 (silicon si) with (fox locos field	USPAT;	2003/08/27 15:07
	1	near (oxide oxidation oxyde oxydation)) near2 mask) not	US-PGPUB;	
	1	((Etching etched etch) near2 substrate with (fox locos field	EPO; JPO; DERWENT;	
1		near (oxide oxidation oxyde oxydation)) near2 mask )		
		/"4620902"   "4000070"   "E021000"   "E00E244"	IBM_TDB USPAT	2003/08/27 15:58
-	8	("4639893"   "4990979"   "5021999"   "5095344"     "5723888"   "5812449"   "5851881"   "6190968").PN.	USPAI	2003/00/27 15.56
		"5723888"   "5812449"   "5851881"   "6190968 J.PN.   6566707.URPN.	USPAT	2003/08/27 15:59
	4200	(438/17,18,11,for.101,for.102,for.142).CCLS.	USPAT;	2003/08/27 15:39
-	4200	( 130/17,10,11,101.101,101.102,101.142).CCL3.	US-PGPUB;	2003/00/27 10.02
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
L	1	<u> </u>	12011 100	1

-	0	(n and p) near3 (substrate silicon si) and	USPAT;	2003/08/27 16:03
		((438/17,18,11,for.101,for.102,for.142).CCLS.)	US-PGPUB;	
1	ł		EPO; JPO;	
			DERWENT;	
	!		IBM_TDB	
-	40	(n and p) near4 (substrate silicon si) and	USPAT;	2003/08/27 16:08
	'	((438/17,18,11,for.101,for.102,for.142).CCLS.)	US-PGPUB;	
	i l	((100)21/120/22/1011202/1011202/1011212/100201/	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	02	(- and -) (aubstrate cilicon si) and	USPAT;	2003/08/27 16:08
-	83	(n and p) near2 (substrate silicon si) and		2003/06/27 10.06
		((438/17,18,11,for.101,for.102,for.142).CCLS.)	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	144	(n and p) near4 (substrate silicon si) and	USPAT;	2003/08/27 16:25
		((438/17,18,11,for.101,for.102,for.142).CCLS.)	US-PGPUB;	
ļ			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1	electron near charge near effect	USPAT;	2003/08/27 17:00
1	1	Cidentifical charge field cheek	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
ŀ				
	_		IBM_TDB	2002/00/27 47-04
-	2	("6143579").PN.	USPAT;	2003/08/27 17:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	breakdown near voltage	USPAT;	2003/08/27 17:01
	,		US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
	1 4	handledown noor voltage	USPAT;	2003/08/27 17:01
-	4	braekdown near voltage	US-PGPUB;	2005/00/27 17:01
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	2002/02/27 17 55
-	42057	breakdown near voltage	USPAT;	2003/08/27 17:02
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
ŀ			IBM_TDB	
_	7870	breakdown near voltage with current	USPAT;	2003/08/27 17:03
			US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT;	1
			IBM_TDB	
	1100	breakdown pear voltage with current with gate	USPAT;	2003/08/27 17:03
-	1168	breakdown near voltage with current with gate		2003/00/2/ 17.03
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	}
	1		IBM_TDB	
-	125	breakdown near voltage with current with gate with	USPAT;	2003/08/27 17:20
		substrate	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
1			IBM_TDB	
L	1		1	·

		· ·		
-	346	dry adj oxide	USPAT;	2003/08/27 17:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	186	dry adj oxide and (438/\$6 257/\$6)	USPAT;	2003/08/27 17:21
	100	ary and order and (100/40 201/40)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	9197	(square rectangle) with (poly si polysilicon silicon)	USPAT;	2003/08/28 09:41
-	313/	(square rectarigle) with (poly st polysilicon stilicon)	US-PGPUB;	2003/00/20 03.41
			EPO; JPO;	
			DERWENT;	
		4.00 (4.7 4.0 4.5 4.0 5 4.0 ) 501.0	IBM_TDB	2002/00/20 00 24
-	4201	(438/17,18,11,for.101,for.102,for.142).CCLS.	USPAT;	2003/08/28 09:34
			US-PGPUB;	
			EPO; JPO;	
ļ			DERWENT;	
			IBM_TDB	
-	38	((square rectangle) with (poly si polysilicon silicon)) and	USPAT;	2003/08/28 09:38
		((438/17,18,11,for.101,for.102,for.142).CCLS.)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
Į.			IBM_TDB	
_	2346	((square rectangle) with (poly si polysilicon silicon)) and	USPAT;	2003/08/28 09:42
	25.15	(438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3)	US-PGPUB;	
		(100)40 201/40) and (001040 detected instanting 11114-17	EPO; JPO;	
			DERWENT;	
1		•	IBM_TDB	
1_	1013	((square rectangle) with (poly si polysilicon silicon)) and	USPAT;	2003/08/28 09:42
1	1013	(438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3)	US-PGPUB;	2000,00,20
		with (poly si polysilicon silicon)	EPO; JPO;	
	ļ	With (poly si polysilicon silicon)	DERWENT;	
			IBM_TDB	
	755	(//course rectangle) with (noty of polycilican cilican)) and	USPAT;	2003/08/28 09:42
-	755	(((square rectangle) with (poly si polysilicon silicon)) and	US-PGPUB;	2003/00/20 03.12
		(438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3)	EPO; JPO;	
		with (poly si polysilicon silicon)) and (poly si polysilicon	DERWENT;	
		silicon) with (pad area pattern)		
1		///annous markenale) with /ach of act william alliams) and	IBM_TDB	2002/09/29 00:42
-	585	(((square rectangle) with (poly si polysilicon silicon)) and	USPAT;	2003/08/28 09:43
		(438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3))	US-PGPUB;	
1		and (fox locos field near (oxide oxidation oxyde oxydation))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	124	((((square rectangle) with (poly si polysilicon silicon)) and	USPAT;	2003/08/28 10:26
		(438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3))	US-PGPUB;	
	1	and (fox locos field near (oxide oxidation oxyde oxydation))	EPO; JPO;	]
		) and (fox locos field near (oxide oxidation oxyde	DERWENT;	
1		oxydation)) same (square rectangle)	IBM_TDB	
-	124	((((square rectangle) with (poly si polysilicon silicon)) and	USPAT;	2003/08/28 10:29
1		(438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3))	US-PGPUB;	
1		and (fox locos field near (oxide oxidation oxyde oxydation))	EPO; JPO;	
		) and (fox locos field near (oxide oxidation oxyde	DERWENT;	
	1	oxydation)) same (square rectangle)	IBM_TDB	

-	51	((((square rectangle) with (poly si polysilicon silicon)) and (438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3)) and (fox locos field near (oxide oxidation oxyde oxydation)) and (fox locos field near (oxide oxidation oxyde oxydation)) same (array) not ((((square rectangle) with (poly si polysilicon silicon)) and (438/\$6 257/\$6) and (sens\$3 detect\$3 measur\$3 test\$3)) and (fox locos field near (oxide oxidation oxyde oxydation)) and (fox locos field near (oxide oxidation oxyde oxydation)) same (square rectangle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 10:49
•	4	monitor\$3 with recycl\$3 with anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 10:50
-	4201	(438/17,18,11,for.101,for.102,for.142).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 11:14
_	3	((438/17,18,11,for.101,for.102,for.142).CCLS.) and (fox locos field near (oxide oxidation oxyde oxydation)) near2 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/28 11:15
-	121	((438/17,18,11,for.101,for.102,for.142).CCLS.) and (fox locos field near (oxide oxidation oxyde oxydation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 11:16